NSN 5961-01-036-3704

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View Online at https://aerobasegroup.com/nsn/5961-01-036-3704 **Inclosure Material:** Metal **Overall Length:** Between 1.470 inches and 1.645 inches Overall Diameter: Between 0.501 inches and 0.505 inches **Mounting Facility Quantity: Internal Configuration:** Junction contact **Electrode Internally-electrically Connected To Case:** Anode **Mounting Method:** Threaded stud **Features Provided:** Hermetically sealed case **Overall Width Across Flats:** Between 0.551 inches and 0.559 inches **Thread Size:** 0.250 inches **Semiconductor Material:** Silicon Voltage Rating In Volts Per Characteristic: 400.0 repetitive peak reverse voltage and 500.0 nonrepetitive peak reverse voltage **Current Rating Per Characteristic:** 35.00 amperes forward current, total rms horsepower metric and 350.00 amperes peak forward surge current nanoamperes **Power Rating Per Characteristic:** 5.0 watts small-signal input power, common-collector outside diameter and 0.5 watts any acceptable peak **Maximum Operating Tempurature Per Measurement Point:** 125.0 degrees celsius junction **Special Features:** Junction pattern arrangement: pnpn **Thread Series Designator:** Unf **Terminal Type And Quantity:** 2 tab, solder lug and 1 threaded stud Shelf Life: N/a **Unit Of Measure:**

No

Demilitarization:

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